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Ratings, Specifications and Waveforms for FACT Data Sheets



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APPLICATION NOTE

Specifying FACT Devices

Traditionally, when a semiconductor manufacturer completed a new device for introduction, specifications were based on the characterization of just a few parts. While these specifications were appealing to the designer, they were often too tight and, over time, the IC manufacturers had difficulty producing devices to the original specs. This forced the manufacturer to relax circuit specifications to reflect the actual performance of the device.

As a result, designers were required to review system designs to ensure the system would remain reliable with the new specifications. Motorola realized and understood the problems associated with characterizing devices too aggressively.

To provide more realistic and manufacturable specs, Motorola devised a systematic and thorough process to generate specifications. Devices are selected from multiple wafer lots to ensure process variations are taken into account. In addition, the process parameters are measured and compared to the known process limits.

This method of characterizing parts more accurately represents the product across time, voltage, temperature and process rather than portraying the fastest possible device. FACT circuits are therefore guaranteed to be manufacturable over time without the need to respecify timing.

These specification guidelines allow designers to design systems more efficiently since the devices used will behave as documented. Unspecified guardbands no longer need to be added by the designer to ensure system reliability.

Power Dissipation — Test Philosophy

In an effort to reduce confusion about measuring C_{PD} , a JEDEC standard test procedure (per JEDEC, Appendix E) has been adopted which specifies the test setup for each type of device. This allows a device to be exercised in a consistent manner for the purpose of specification comparison. All device measurements are made with $V_{CC} = 5\text{ V}$ at 25°C , with 3-state outputs both enabled and disabled.

Gates — Switch one input. Bias the remaining inputs such that the output switches.

Latches — Switch the Enable and D inputs such that the latch toggles.

Flip-Flops — Switch the clock pin while changing D (or bias J and K) such that the output(s) change each clock cycle. For parts with a common clock, exercise only one flip-flop.

Decoders — Switch one address pin which changes two outputs.

Multiplexers — Switch one address pin with the corresponding data inputs at opposite logic levels so that the output switches.

Counters — Switch the clock pin with other inputs biased such that the device counts.

Shift Registers — Switch the clock pin with other inputs biased such that the device counts.

Transceivers — Switch one data input. For bidirectional devices enable only one direction.

Parity Generator — Switch one input.

Priority Encoders — Switch the lowest priority input.

Load Capacitance — Each output which is switching should be loaded with the standard 50 pF.

If the device is tested at a high enough frequency, the static supply current can be ignored. Thus at 1 MHz, the following formula can be used to calculate C_{PD} :

$$C_{PD} = I_{CC}/(V_{CC}) (1 \times 10^6) - \text{Equivalent Load Capacitance}$$

AND8277/D

Ratings and Specifications

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Source/Sink Current, per Pin	± 50	mA
I_{CC}	DC V_{CC} or GND Current per Output Pin	± 50	mA
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

¹ Absolute maximum ratings are those values beyond which damage to the device may occur. Obviously the databook specifications should be met, without exception to ensure that the system design is reliable over its power supply, temperature, output/input loading variables. Motorola does not recommend operation of FACT circuits outside databook specifications.

Figure 3-1. Absolute Maximum Ratings¹

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit	
V_{CC}	Supply Voltage	'AC	2.0	5.0	6.0	V
		'ACT	4.5	5.0	5.5	
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Ref. to GND)	0		V_{CC}	V	
t_r, t_f	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V_{CC} @ 3.0 V		150		ns/V
		V_{CC} @ 4.5 V		40		
		V_{CC} @ 5.5 V		25		
t_r, t_f	Input Rise and Fall Time (Note 2) 'ACT Devices except Schmitt Inputs	V_{CC} @ 4.5 V		10		ns/V
		V_{CC} @ 5.5 V		8.0		
T_J	Junction Temperature (PDIP)			140	$^{\circ}\text{C}$	
T_A	Operating Ambient Temperature Range	-40	25	85	$^{\circ}\text{C}$	
I_{OH}	Output Current — High			-24	mA	
I_{OL}	Output Current — Low			24	mA	

- V_{in} from 30% to 70% V_{CC} ; see individual Data Sheets for devices that differ from the typical input rise and fall times.
- V_{in} from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

Figure 3-2. Recommended Operating Conditions

AND8277/D

DC CHARACTERISTICS for 'AC Family Devices

Symbol	Parameter	V _{CC} (V)	74AC		74AC		Unit	Conditions
			T _A = +25°C		T _A = -40°C to +85°C			
			Typ	Guaranteed Limits				
V _{IH}	Minimum High Level Input Voltage	3.0	1.5	2.1	2.1		V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V
		4.5	2.25	3.15	3.15			
		5.5	2.75	3.85	3.85			
V _{IL}	Maximum Low Level Input Voltage	3.0	1.5	0.9	0.9		V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V
		4.5	2.25	1.35	1.35			
		5.5	2.75	1.65	1.65			
V _{OH}	Minimum High Level Output Voltage	3.0	2.99	2.9	2.9		V	I _{OUT} = -50 μA
		4.5	4.49	4.4	4.4			
		5.5	5.49	5.4	5.4			
		3.0		2.56	2.46		V	*V _{IN} = V _{IL} or V _{IH} -12 mA I _{OH} -24 mA -24 mA
		4.5		3.86	3.76			
		5.5		4.86	4.76			
V _{OL}	Maximum Low Level Output Voltage	3.0	0.002	0.1	0.1		V	I _{OUT} = 50 μA
		4.5	0.001	0.1	0.1			
		5.5	0.001	0.1	0.1			
		3.0		0.36	0.44		V	*V _{IN} = V _{IL} or V _{IH} 12 mA I _{OL} 24 mA 24 mA
		4.5		0.36	0.44			
		5.5		0.36	0.44			
I _{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0		μA	V _I = V _{CC} , GND
I _{OLD}	†Minimum Dynamic Output Current	5.5			75		mA	V _{OLD} = 1.65 V Max
I _{OHD}		5.5			-75		mA	V _{OHD} = 3.85 V Min
I _{CC}	Maximum Quiescent Supply Current	5.5		8.0	80		μA	V _{IN} = V _{CC} or GND

* All outputs loaded; thresholds on input associated with output under test.

† Maximum test duration 2.0 ms, one output loaded at a time.

Note: I_{IN} and I_{CC} @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V_{CC}.

DC CHARACTERISTICS for 'ACT Family Devices

Symbol	Parameter	V _{CC} (V)	74ACT		74ACT		Unit	Conditions
			T _A = 25°C		T _A = -40°C to +85°C			
			Typ	Guaranteed Limits	Typ	Guaranteed Limits		
V _{IH}	Minimum High Level Input Voltage	4.5	1.5	2.0	2.0	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
		5.5	1.5	2.0	2.0			
V _{IL}	Maximum Low Level Input Voltage	4.5	1.5	0.8	0.8	V	V _{OUT} = 0.1 V or V _{CC} - 0.1 V	
		5.5	1.5	0.8	0.8			
V _{OH}	Minimum High Level Output Voltage	4.5	4.49	4.4	4.4	V	I _{OUT} = -50 μA	
		5.5	5.49	5.4	5.4			
		4.5		3.86	3.76	V	*V _{IN} = V _{IL} or V _{IH} -24 mA	
		5.5		4.86	4.76			
V _{OL}	Maximum Low Level Output Voltage	4.5	0.001	0.1	0.1	V	I _{OUT} = 50 μA	
		5.5	0.001	0.1	0.1			
		4.5		0.36	0.44	V	*V _{IN} = V _{IL} or V _{IH} 24 mA	
		5.5		0.36	0.44			
I _{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	μA	V _I = V _{CC} , GND	
ΔI _{CC}	Additional Max. I _{CC} /Input	5.5	0.6		1.5	mA	V _I = V _{CC} - 2.1V	
I _{OLD}	†Minimum Dynamic Output Current	5.5			75	mA	V _{OLD} = 1.65 V Max	
I _{OHD}		5.5			-75	mA	V _{OHD} = 3.85 V Min	
I _{CC}	Maximum Quiescent Supply Current	5.5		8.0	80	μA	V _{IN} = V _{CC} or GND	

* All outputs loaded; thresholds on input associated with output under test.
 † Maximum test duration 2.0 ms, one output loaded at a time.

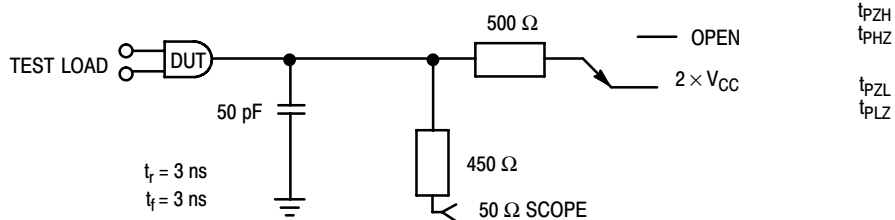


Figure 3-3. AC Tri-State Loading Circuit

AC Loading and Waveforms

Loading Circuit

Figure 3-3 shows the AC loading circuit used in characterizing and specifying propagation delays of all FACT devices ('AC and 'ACT) unless otherwise specified in the data sheet of a specific device.

The use of this load, differs somewhat from previous (HCMOS) practice, provides more meaningful information and minimizes problems of instrumentation and customer correlation. In the past, +25°C propagation delays for TTL devices were specified with a load of 15 pF to ground; this required great care in building test jigs to minimize stray capacitance and implied the use of high impedance, high frequency scope probes. FAST circuits changed to 50 pF of capacitance allowing more leeway in stray capacitance and

also loading the device during rising or falling output transitions. This more closely resembles the inloading to be expected in average applications and thus gives the designer more useful delay figures. We have incorporated this scheme into the FACT product line. The net effect of the change in AC load is to increase the average observed propagation delay by about 1 ns.

The 500 ohm resistor to ground can be a high frequency passive probe for a sampling oscilloscope, which costs much less than the equivalent high impedance probe. Alternately, the 500 ohm resistor to ground can simply be a 450 ohm resistor feeding into a 50 ohm coaxial cable leading to a sampling scope input connector, with the internal 50 ohm termination of the scope completing the path to ground. This

is the preferred scheme for correlation. (See Figure 3-3.) With this scheme there should be a matching cable from the device input pin to the other input of the sampling scope; this also serves as a 50 ohm termination for the pulse generator that supplies the input signal.

Shown in Figure 3-3 is a second 500 ohm resistor from the device output to a switch. For most measurements this

switch is open; it is closed for measuring one set of the Enable/Disable parameters (LOW-to-OFF and OFF-to-LOW) of a 3-state output. With the switch closed, the pair of 500 ohm resistors and the $2 \times V_{CC}$ supply voltage establish a quiescent HIGH level.

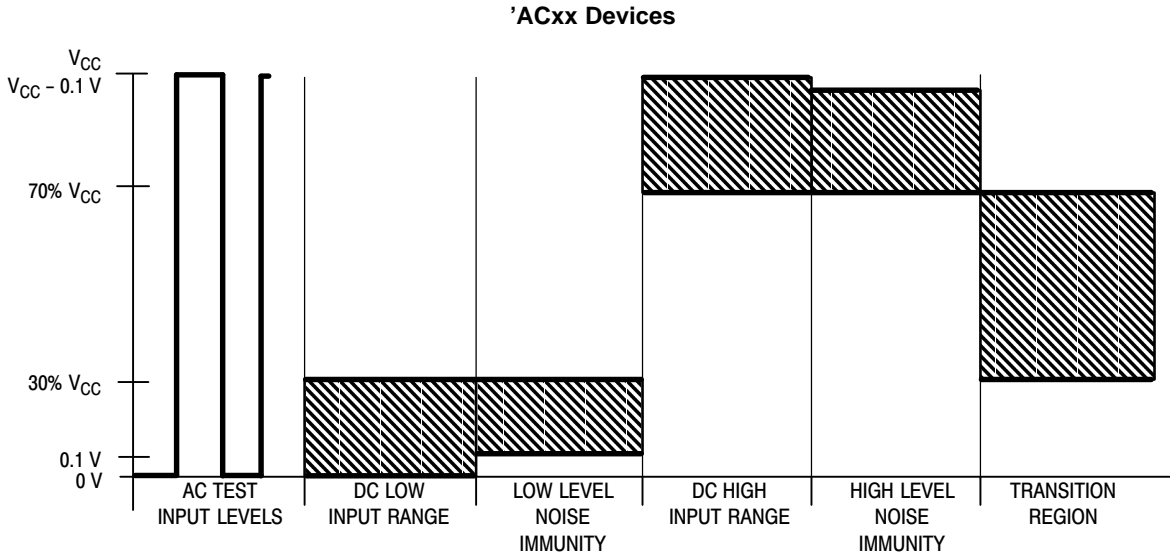


Figure 3-4a. Test Input Signal Levels

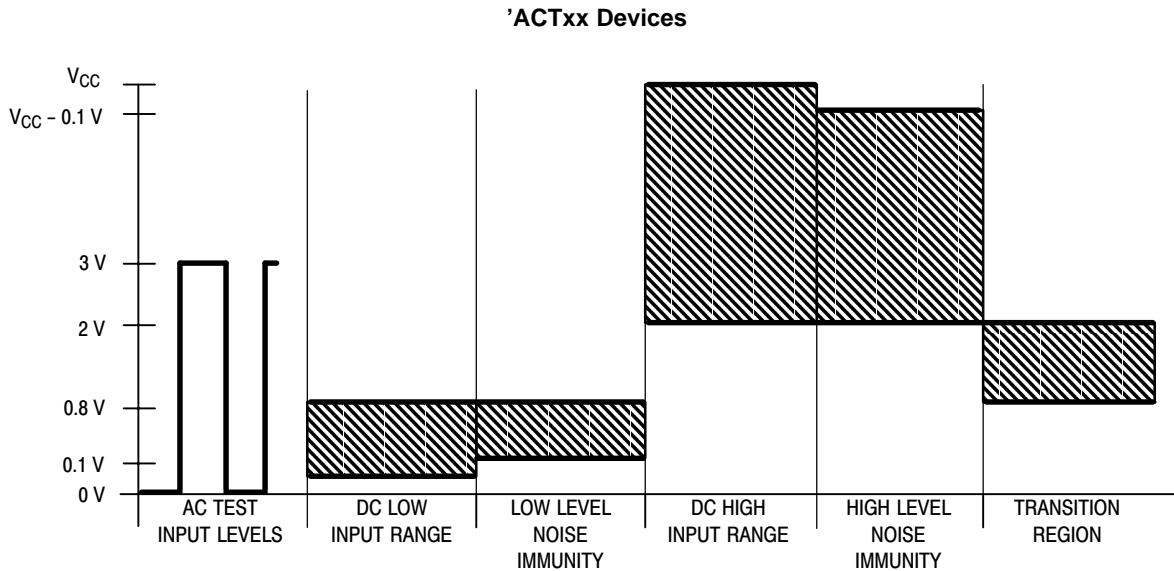


Figure 3-4b. Test Input Signal Levels

Test Conditions

Figures 3-4a and 3-4b describe the input signal voltage levels to be used when testing FACT circuits. The AC test conditions follow industry convention requiring V_{IN} to range from 0 V for a logic LOW to 3 V for a logic HIGH for 'ACT devices and 0 V to V_{CC} for 'AC devices. The DC parameters are normally tested with V_{IN} at guaranteed input levels, that is V_{IH} to V_{IL} (see data tables for details). Care must be taken to adequately decouple these high performance parts and to protect the test signals from electrical noise. In an electrically noisy environment, (e.g., a tester and handler not specifically designed for high speed work), DC input levels may need to be adjusted to increase the noise margin to allow for the extra noise in the tester which would not be seen in a system.

Noise immunity testing is performed by raising V_{IN} to the nominal supply voltage of 5 V then dropping to a level corresponding to V_{IH} characteristics, and then raising again to the 5 V level. Noise tests can also be performed on the V_{IL} characteristics by raising V_{IN} from 0 V to V_{IL} , then returning to 0 V. Both V_{IH} and V_{IL} noise immunity tests should not induce a switch condition on the appropriate outputs of the FACT device.

Good high frequency wiring practices should be used in constructing test jigs. Leads on the load capacitor should be as short as possible to minimize ripples on the output wave form transitions and to minimize undershoot. Generous ground metal (preferably a ground plane) should be used for the same reasons. A V_{CC} bypass capacitor should be provided at the test socket, also with minimum lead lengths.

Rise and Fall Times

Input signals should have rise and fall times of 3 ns and signal swing of 0 V to 3.0 V V_{CC} for 'ACT devices or 0 V to V_{CC} for 'AC devices. Rise and fall times less than or equal to 1 ns should be used for testing f_{max} or pulse widths.

CMOS devices, including 4000 Series CMOS, HC, HCT and FACT families, tend to oscillate when the input rise and fall times become lengthy. As a direct result of its increased performance, FACT devices can be more sensitive to slow input rise and fall times than other lower performance technologies.

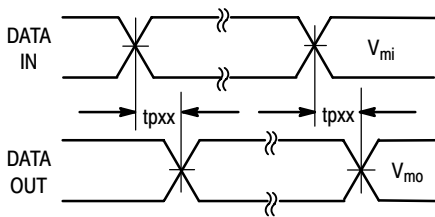


Figure 3-5. Waveform for Inverting and Non-Inverting Functions

* V_{mi} = 50% V_{CC} for 'AC devices; 1.5 V for 'ACT devices
 V_{mo} = 50% for 'AC/ACT devices

It is important to understand why this oscillation occurs. Consider the outputs, where the problem is initiated. Usually, CMOS outputs drive capacitive loads with low DC leakage. When the output changes from a HIGH level to a LOW level, or from a LOW level to a HIGH level, this capacitance has to be charged or discharged. With the present high performance technologies, this charging or discharging takes place in a very short time, typically 2–3 ns. The requirement to charge or discharge the capacitive loads quickly creates a condition where the instantaneous current change through the output structure is quite high. A voltage is generated across the V_{CC} or ground leads inside the package due to the inductance of these leads. The internal ground of the chip will change in reference to the outside world because of this induced voltage.

Consider the input. If the internal ground changes, the input voltage level appears to change to the DUT. If the input rise time is slow enough, its level might still be in the device threshold region, or very close to it, when the output switches. If the internally-induced voltage is large enough, it is possible to shift the threshold region enough so that it re-crosses the input level. If the gain of the device is sufficient and the input rise or fall time is slow enough, then the device may go into oscillation. As device propagation delays become shorter, the inputs will have less time to rise or fall through the threshold region. As device gains increase, the outputs will swing more, creating more induced voltage. Instantaneous current change will be greater as outputs become quicker, generating more induced voltage.

Package-related causes of output oscillation are not entirely to blame for problems with input rise and fall time measurements. All testers have V_{CC} and ground leads with a finite inductance. This inductance needs to be added to the inductance in the package to determine the overall voltage which will be induced when the outputs change. As the reference for the input signals moves further away from the pin under test, the test will be more susceptible to problems caused by the inductance of the leads and stray noise. Any noise on the input signal will also cause problems. With FACT logic having gains as high as 100, it merely takes a 50 mV change in the input to generate a full 5 V swing on the output.

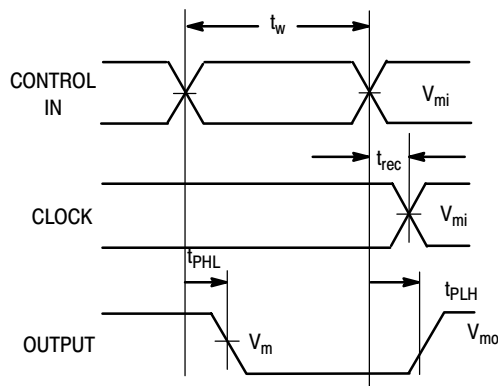


Figure 3-6. Propagational Delay, Pulse Width and t_{rec} Waveforms

Enable and Disable Times

Figures 3-8 and 3-9 show that the disable times are measured at the point where the output voltage has risen or fallen by 10% from the voltage rail level (i.e., ground for t_{PLZ} or V_{CC} for t_{PHZ}). This change enhances the repeatability of measurements, reduces test times, and gives the system designer more realistic delay times to use in calculating minimum cycle times. Since the high impedance state rising or falling waveform is RC-controlled, the first 10% of change is more linear and is less susceptible to external influences. More importantly, perhaps from the system designer's point of view, a change in voltage of 10% is adequate to ensure that a device output has turned OFF. Measuring to a larger change in voltage merely exaggerates the apparent Disable time and thus penalizes system performance since the designer must use the Enable and Disable times to devise worst case timing signals to ensure that the output of one device is disabled before that of another device is enabled.

Propagation Delay, f_{max} , Set, Hold, and Recovery Times

A 1 MHz square wave is recommended for most propagation delay tests. The repetition rate must necessarily be increased for testing f_{max} . A 50% duty cycle should always be used when testing f_{max} . Two pulse generators are usually required for testing such parameters as setup time (t_s), hold time (t_h), recovery time (t_{REC}) shown in Figure 9.

Electrostatic Discharge

Precautions should be taken to prevent damage to devices by electrostatic discharge. Static charge tends to accumulate on insulated surfaces such as synthetic fabrics or carpeting, plastic sheets, trays, foam, tubes or bags, and on ungrounded electrical tools or appliances. The problem is much worse in a dry atmosphere. In general, it is recommended that individuals take the precaution of touching a known ground before handling devices. To effectively avoid electrostatic damage to FACT devices, it is recommended that individuals wear a grounded wrist strap when handling devices. More often, handling equipment, which is not properly grounded, causes damage to parts. Ensure that all plastic parts of the tester, which are near the device, are conductive and connected to ground.

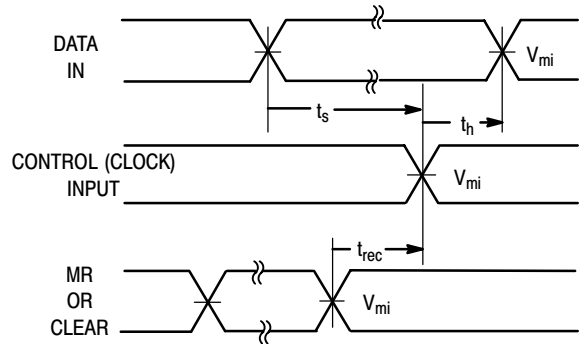


Figure 3-7. Setup Time, Hold Time and Recovery Time

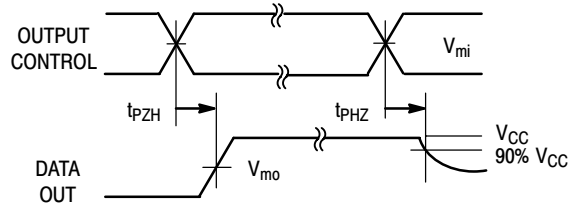


Figure 3-8. 3-State Output High Enable and Disable Times

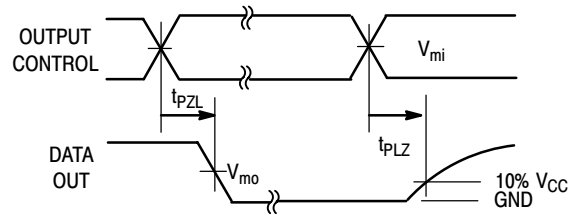



Figure 3-9. 3-State Output Low Enable and Disable Times

* V_{mi} = 50% V_{CC} for 'AC devices; 1.5 V for 'ACT devices
 V_{mo} = 50% V_{CC} for 'AC/'ACT devices

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